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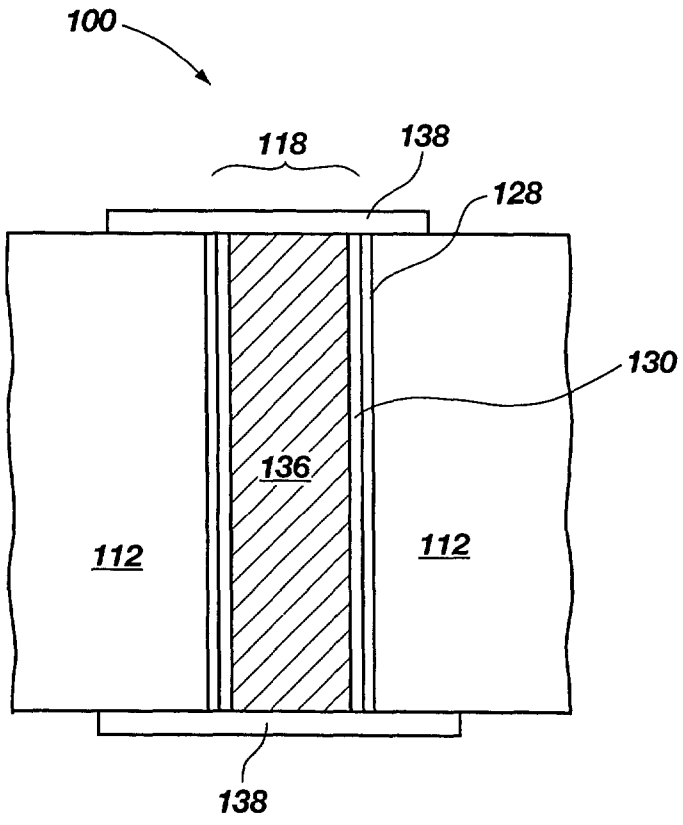
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(54) Title: PROCESS AND INTEGRATION SCHEME FOR FABRICATING CONDUCTIVE COMPONENTS THROUGH-VIAS AND SEMICONDUCTOR COMPONENTS INCLUDING CONDUCTIVE THROUGH-WAFER VIAS



(57) Abstract: A method for forming a conductive via in a semiconductor component is disclosed. The method includes providing a substrate (112) having a first surface and an opposing, second surface. At least one hole (118) is formed in the substrate extending between the first surface and the opposing, second surface. A seed layer (128) is formed on a sidewall defining the at least one hole of the substrate and coated with a conductive layer (130), and a conductive or nonconductive filler material (136) is introduced into the remaining space within the at least one hole. A method of forming a conductive via through a substrate using a blind hole is also disclosed. Semiconductor components and electronic systems having substrates including the conductive via of the present invention are also disclosed.

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